AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph at lines 11-37 of page 5 with the following amended paragraph:

A semiconductor chip 11 having a first and a second main electrode is situated between an electrically conductive baseplate 91, which forms a second main connection of the power semiconductor module, and an electrically conductive covering plate 92, which forms a first main connection of the power semiconductor module. First and second main electrodes have a first and second electrode metallization ~~11 and~~ 12 and 13, respectively. A contact lamina 2 is situated between first main electrode and covering plate 92, said contact lamina being coated with a protective layer comprising a base layer 31 and a surface layer 32. The module is closed off by side walls 93, in which case this closure need not necessarily be hermetic. In this case, a first thickness of the contact lamina 2 preferably amounts to at least half of a second thickness of the semiconductor chip 11. In this case, the contact lamina 2 may advantageously be obtained by cutting out or stamping out from a foil. Preferably, however, use is made of an even thicker contact lamina 2 having a first thickness in the range of a few tenths of a millimeter to a few millimeters, preferably having a first thickness of approximately one millimeter. In this case, the contact lamina 2 may advantageously be produced by cutting out or stamping out from a metal sheet.

Please replace the paragraph at lines 13-36 of page 7 with the following amended paragraph:

In a preferred refinement of the invention, the surface layer 32 substantially comprises Rh, Ru or an electrically conductive nitride, preferably TiN, CrN or ZrN. At customary operating temperatures, Rh has only very weak diffusion, and Ru and nitride even have no diffusion at all, at contacts with a first electrode metallization ~~11~~ 12 made of Ag. The formation of a fixed material connection between first electrode metallization ~~11~~ 12 and contact lamina 2 is thus prevented in a particularly effective manner. If the contact lamina 2 substantially comprises Al or Mg and the surface layer 32 substantially comprises Ru, the base layer 31 is advantageously somewhat thicker, preferably approximately between 6 µm and 15 µm. This is important particularly when Ru is deposited in an Ru bath in which a pH value of approximately 1 typically prevails, and which is highly chemically aggressive for this reason. Moreover, a thin gold layer is advantageously provided between the base layer 31 made of Ni and the surface layer 32 in order to improve an adhesion between Ni and Ru. In this case, a fifth thickness of the gold layer preferably lies in the region of a few tenths of a micrometer; it is preferably approximately 0.2 micrometer.